

Appl. No. 09/837,022  
Amdt. Dated September 18, 2003  
Reply to Office Action of July 1, 2003

**Amendment to the Claims:**

This listing will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1-4 (previously canceled):

Claim 5 (currently amended): A method of manufacturing a semiconductor device comprising the steps of:

forming an electrodeposition frame on a flexible flat metallic substrate, said electrodeposition frame having first metallic layers and second metallic layers for external extension being patterned, wherein said first metallic layers are thicker than said second metallic layers;

contiguously monitoring mounting a plurality of semiconductor elements, each with electrode pads thereon, on said first metallic layers;

wire-bonding the electrode pads to said second metallic layers which are located between said semiconductor elements;

resin-sealing said semiconductor elements mounted on said electrodeposition frame;

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removing said metallic substrate to provide a resin sealing body having a bottom so that rear surfaces of the first metallic layers and second metallic layers are flush with the bottom of said resin sealing body;

cutting said resin sealing body into individual semiconductor devices, wherein each device is provided with the first and second metallic layers; and

depositing metallic thin films on portions of the first and second metallic layers that are exposed at the bottom said resin sealing body.

Claim 6 (original): A method of manufacturing a semiconductor device according to claim 5, further comprising after the step of cutting, the step of:

depositing metallic layers for electrodes to the second metallic layers exposed from a rear surface of said resin sealing body.

Claim 7 (original): A method of manufacturing a semiconductor device according to claim 5, wherein

in said step of cutting of said resin sealing body, it is cut along a center line of each of the second metallic layers to provide metallic layers for external extension for adjacent semiconductor elements.

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**Claim 8 (original): A method of manufacturing a semiconductor device according to claim 5, wherein said electrodeposition frame is resin sealed together with said semiconductor elements using said metallic substrate as a lower die.**

**Claim 9 (previously canceled)**